

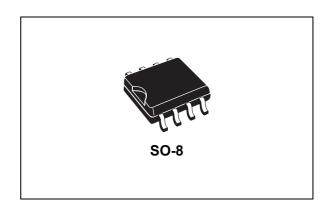
### VN750PS-E

### High-side driver

#### **Features**

Туре	R <sub>DS(on)</sub>	I <sub>OUT</sub>	V <sub>CC</sub>
VN750PS-E	60 m $Ω$	6 A	36 V

- ECOPACK®: lead free and RoHS compliant
- Automotive Grade: compliance with AEC guidelines
- CMOS compatible input
- On-state open-load detection
- Off-state open-load detection
- Shorted load protection
- Undervoltage and overvoltage shutdown
- Protection against loss of ground
- Very low standby current
- Reverse battery protection



### **Description**

The VN750PS-E is a monolithic device designed in STMicroelectronics™ VIPower™ M0-3 Technology intended for driving any kind of load with one side connected to ground.

Active V<sub>CC</sub> pin voltage clamp protects the device against low energy spikes (see ISO7637 transient compatibility table). Active current limitation combined with thermal shutdown and automatic restart help protect the device against overload.

The device detects open load condition in on and off-state. Output shorted to  $V_{CC}$  is detected in the off-state. Device automatically turns off in case of ground pin disconnection.

Table 1. Device summary

Package	Order codes		
1 ackage	Tube	Tape and reel	
SO-8	VN750PS-E	VN750PSTR-E	

Contents VN750PS-E

## **Contents**

1	Block	diagram and pin description 5
2	Electi	rical specifications
	2.1	Absolute maximum ratings 6
	2.2	Thermal data 7
	2.3	Electrical characteristics
	2.4	Electrical characteristics curves
	2.5	GND protection network against reverse battery
	2.6	Load dump protection
	2.7	Microcontroller I/Os protection
	2.8	Open-load detection in off-state
	2.9	SO-8 maximum demagnetization energy (V <sub>CC</sub> = 13.5 V) 19
3	Packa	age and PCB thermal data
	3.1	SO-8 thermal data
4	Packa	age and packing information
	4.1	SO-8 package information
	4.2	SO-8 packing information
5	Revis	ion history

VN750PS-E List of tables

# List of tables

Table 1.	Device summary	1
Table 2.	Suggested connections for unused and not connected pins	5
Table 3.	Absolute maximum ratings	6
Table 4.	Thermal data	7
Table 5.	Electrical characteristics	8
Table 6.	Truth table	. 10
Table 7.	Electrical transient requirements on V <sub>CC</sub> pin (part 1/3)	. 11
Table 8.	Electrical transient requirements on V <sub>CC</sub> pin (part 2/3)	. 11
Table 9.	Electrical transient requirements on V <sub>CC</sub> pin (part 3/3)	. 11
Table 10.	Thermal parameter	
Table 11.	SO-8 mechanical data	. 24
Table 12.	Document revision history	. 26

List of figures VN750PS-E

# List of figures

Figure 1.	Block diagram5
Figure 2.	Configuration diagram (top view)
Figure 3.	Current and voltage conventions
Figure 4.	Status timings
Figure 5.	Switching time waveforms
Figure 6.	Waveforms
Figure 7.	Off-state output current
Figure 8.	High level input current
Figure 9.	Input clamp voltage13
Figure 10.	Status leakage current
Figure 11.	Status low output voltage
Figure 12.	Status clamp voltage
Figure 13.	On-state resistance vs T <sub>case</sub> 14
Figure 14.	On-state resistance vs V <sub>CC</sub>
Figure 15.	Open-load on-state detection threshold
Figure 16.	Input high level
Figure 17.	Input low level
Figure 18.	Input hysteresis voltage
Figure 19.	Overvoltage shutdown
Figure 20.	Open-load off-state voltage detection threshold
Figure 21.	Turn-on voltage slope
Figure 22.	Turn-off voltage slope
Figure 23.	I <sub>lim</sub> vs T <sub>case</sub>
Figure 24.	Application schematic
Figure 25.	Open-load detection in off-state
Figure 26.	SO-8 maximum turn-off current versus inductance
Figure 27.	PC board
Figure 28.	Rthj-amb vs PCB copper area in open box free air condition
Figure 29.	SO-8 thermal impedance junction ambient single pulse
Figure 30.	Thermal fitting model of a single channel
Figure 31.	SO-8 package dimensions
Figure 32.	SO-8 tube shipment (no suffix)
Figure 33.	SO-8 tape and reel shipment (suffix "TR")

## 1 Block diagram and pin description

Figure 1. Block diagram

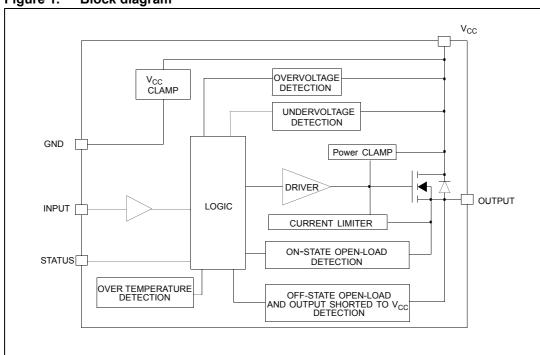


Figure 2. Configuration diagram (top view)

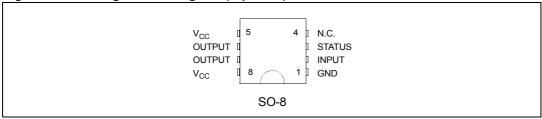


Table 2. Suggested connections for unused and not connected pins

Connection/pin	Status	N.C.	Output	Input
Floating	Х	Х	Х	Х
To ground		Х		Through 10 K $\Omega$ resistor

#### **Electrical specifications** 2

 $I_S$  $V_{\mathsf{F}}$  ${\rm I}_{\rm IN}$  $V_{CC}$ INPUT  $I_{STAT}$  $I_{OUT}$ T STATUS OUTPUT [  $V_{CC}$ GND  $V_{IN}$  $V_{OUT}$  $V_{\text{STAT}}$ ↓ I<sub>GND</sub>

Figure 3. **Current and voltage conventions** 

#### 2.1 **Absolute maximum ratings**

Stress values that exceed those listed in the "Absolute maximum ratings" table can cause permanent damage to the device. These are stress ratings only and operation of the device at these or any other conditions greater than those indicated in the operating sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Refer also to the STMicroelectronics sure program and other relevant quality documents.

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	DC supply voltage	41	V
-V <sub>CC</sub>	Reverse DC supply voltage	- 0.3	V
-I <sub>gnd</sub>	DC reverse ground pin current	- 200	mA
I <sub>OUT</sub>	DC output current	Internally limited	Α
-I <sub>OUT</sub>	Reverse DC output current	- 6	Α
I <sub>IN</sub>	DC input current	+/-10	mA
I <sub>STAT</sub>	DC status current	+/- 10	mA
V <sub>ESD</sub>	Electrostatic discharge (human body model: R = 1.5 KΩ; C = 100 pF) - Input - Status - Output - V <sub>CC</sub>	4000 4000 5000 5000	> > >

Table 3. Absolute maximum ratings (continued)

Symbol	Parameter	Value	Unit
E <sub>MAX</sub>	Maximum switching energy (L = 1.8 mH; $R_L = 0 \Omega$ ; $V_{bat} = 13.5 V$ ; T <sub>jstart</sub> = 150 °C; $I_L = 9 A$ )  Power dissipation $T_C = 25$ °C 4.2		mJ
P <sub>tot</sub>	Power dissipation T <sub>C</sub> = 25 °C	4.2	W
T <sub>j</sub>	Junction operating temperature	Internally limited	°C
T <sub>c</sub>	Case operating temperature	- 40 to 150	°C
T <sub>stg</sub>	Storage temperature	- 55 to 150	°C

### 2.2 Thermal data

Table 4. Thermal data

Symbol	Parameter	Max. value	Unit
R <sub>thj-lead</sub>	Thermal resistance junction-lead	30	°C/W
D	Thormal resistance junction ambient	93 <sup>(1)</sup>	°C/W
R <sub>thj-amb</sub>	Thermal resistance junction-ambient	82 <sup>(2)</sup>	°C/W

When mounted on a standard single-sided FR-4 board with 0.5 cm<sup>2</sup> of Cu (at least 35 μm thick) connected to all V<sub>CC</sub> pins. Horizontal mounting and no artificial air flow.

<sup>2.</sup> When mounted on a standard single-sided FR-4 board with 2 cm $^2$  of Cu (at least 35  $\mu$ m thick) connected to all V<sub>CC</sub> pins. Horizontal mounting and no artificial air flow.

### 2.3 Electrical characteristics

Values specified in this section are for 8 V < V<sub>CC</sub> < 36 V; -40  $^{\circ}$ C < T<sub>j</sub> < 150  $^{\circ}$ C, unless otherwise stated.

Table 5. Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
Power				<b>.</b>		
V <sub>CC</sub>	Operating supply voltage		5.5	13	36	٧
V <sub>USD</sub>	Undervoltage shutdown		3	4	5.5	٧
V <sub>USDhyst</sub>	Undervoltage shutdown hysteresis			0.5		٧
V <sub>OV</sub>	Overvoltage shutdown		36			٧
R <sub>ON</sub>	On-state resistance	$I_{OUT}$ = 2 A; $T_j$ = 25 °C; $V_{CC}$ > 8 V			60	mΩ
		$I_{OUT} = 2 A; V_{CC} > 8 V$			120	mΩ
		Off-state; $V_{CC} = 13 \text{ V}$ ; $V_{IN} = V_{OUT} = 0 \text{ V}$		10	25	μΑ
I <sub>S</sub>	Supply current	Off-state; $V_{CC} = 13 \text{ V}$ ; $V_{IN} = V_{OUT} = 0 \text{ V}$ ; $T_j = 25 ^{\circ}\text{C}$		10	20	μΑ
		On-state; $V_{CC} = 13 \text{ V}$ ; $V_{IN} = 5 \text{ V}$ ; $I_{OUT} = 0 \text{ A}$		2	3.5	mA
I <sub>L(off1)</sub>	Off-state output current	$V_{IN} = V_{OUT} = 0 V$	0		50	μA
I <sub>L(off2)</sub>	Off-state output current	$V_{IN} = 0 \text{ V}; V_{OUT} = 3.5 \text{ V}$	-75		0	μΑ
I <sub>L(off3)</sub>	Off-state output current	$V_{IN} = V_{OUT} = 0 \text{ V}; V_{CC} = 13 \text{ V}; $ $T_j = 125 \text{ °C}$			5	μΑ
I <sub>L(off4)</sub>	Off-state output current	$V_{IN} = V_{OUT} = 0 \text{ V}; V_{CC} = 13 \text{ V}; $ $T_j = 25 \text{ °C}$			3	μΑ
Switching (V	<sub>CC</sub> = 13V)					
t <sub>d(on)</sub>	Turn-on delay time	$R_L$ = 6.5 $\Omega$ from $V_{IN}$ rising edge to $V_{OUT}$ = 1.3 $V$		40		μs
t <sub>d(off)</sub>	Turn-off delay time	$R_L$ = 6.5 Ω from $V_{IN}$ falling edge to $V_{OUT}$ = 11.7 $V$		30		μs
dV <sub>OUT</sub> /dt <sub>(on)</sub>	Turn-on voltage slope	$R_L$ = 6.5 $\Omega$ from $V_{OUT}$ = 1.3 $V$ to $V_{OUT}$ = 10.4 $V$	S	ee <i>Figure 2</i>	21	V/µs
dV <sub>OUT</sub> /dt <sub>(off)</sub>	Turn-off voltage slope	$R_L = 6.5 \Omega$ from $V_{OUT} = 11.7 V$ to $V_{OUT} = 1.3 V$	See Figure 22		V/µs	
Input pin						
V <sub>IL</sub>	Input low level				1.25	V
I <sub>IL</sub>	Low level input current	V <sub>IN</sub> = 1.25 V	1			μΑ
V <sub>IH</sub>	Input high level		3.25			٧

Table 5. Electrical characteristics (continued)

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I <sub>IH</sub>	High level input current	V <sub>IN</sub> = 3.25 V			10	μΑ
V <sub>hyst</sub>	Input hysteresis voltage		0.5			V
V	Input clamp voltage	I <sub>IN</sub> = 1 mA	6	6.8	8	V
V <sub>ICL</sub>	Input clamp voltage	I <sub>IN</sub> = -1 mA		-0.7		V
V <sub>CC</sub> output	diode					
V <sub>F</sub>	Forward on voltage	-I <sub>OUT</sub> = 1.3 A; T <sub>j</sub> = 150 °C			0.6	V
Status pin				•		
V <sub>STAT</sub>	Status low output voltage	I <sub>STAT</sub> = 1.6 mA			0.5	V
I <sub>LSTAT</sub>	Status leakage current	Normal operation; V <sub>STAT</sub> = 5 V			10	μΑ
C <sub>STAT</sub>	Status pin input capacitance	Normal operation; V <sub>STAT</sub> = 5 V			100	pF
V	Status alama valtaga	I <sub>STAT</sub> = 1 mA	6	6.8	8	V
V <sub>SCL</sub>	Status clamp voltage	I <sub>STAT</sub> = -1 mA		-0.7		V
Protections <sup>6</sup>	(1)					
T <sub>TSD</sub>	Shutdown temperature		150	175	200	°C
T <sub>R</sub>	Reset temperature		135			°C
T <sub>hyst</sub>	Thermal hysteresis		7	15		°C
t <sub>SDL</sub>	Status delay in overload condition	T <sub>j</sub> >T <sub>jsh</sub>			20	ms
-	Current limitation	9 V <v<sub>CC&lt;36 V</v<sub>	6	9	15	Α
I <sub>lim</sub>	Current innitation	5 V <v<sub>CC&lt;36 V</v<sub>			15	Α
V <sub>demag</sub>	Turn-off output clamp voltage	I <sub>OUT</sub> = 2 A; V <sub>IN</sub> = 0 V; L = 6 mH	V <sub>CC</sub> -41	V <sub>CC</sub> -48	V <sub>CC</sub> -55	٧
Open-load d	letection					
I <sub>OL</sub>	Open-load on-state detection threshold	V <sub>IN</sub> = 5 V	50		200	mA
t <sub>DOL(on)</sub>	Open-load on-state detection delay	I <sub>OUT</sub> = 0 A			200	μs
V <sub>OL</sub>	Open-load off-state voltage detection threshold	V <sub>IN</sub> = 0 V	1.5		3.5	٧
t <sub>DOL(off)</sub>	Open-load detection delay at turn-off				1000	μs

To ensure long term reliability under heavy overload or short circuit conditions, protection and related diagnostic signals
must be used together with a proper software strategy. If the device operates under abnormal conditions this software must
limit the duration and number of activation cycles.

Figure 4. Status timings

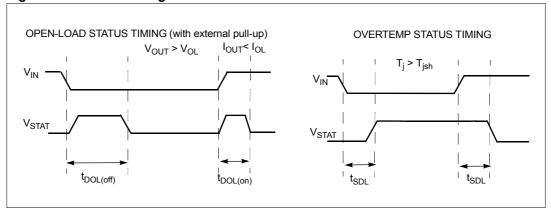


Figure 5. Switching time waveforms

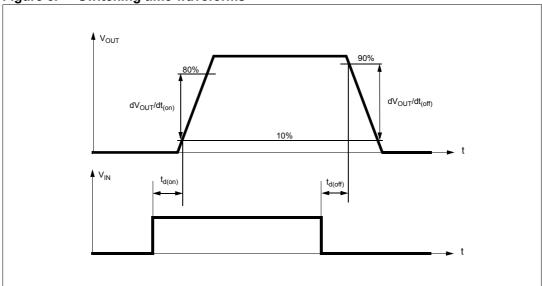


Table 6. Truth table

Conditions	Input	Output	Status
Normal operation	L	L 	H
-	Н	Н	Н
	L	L	Н
Current limitation	Н	X	$(T_j < T_{TSD}) H$ $(T_j > T_{TSD}) L$
	Н	X	$(T_j > T_{TSD}) L$
Over temperature	L	L	Н
Over temperature	Н	L	L
Undervoltage	L	L	X
Undervoltage	Н	L	Х
Overvoltage	L	L	Н
Overvoitage	Н	L	Н

Table 6. Truth table (continued)

Conditions	Input	Output	Status
Output voltage > V <sub>OL</sub>	L	Н	L
Output voltage > vol	Н	Н	Н
Output ourrent + I	L	L	Н
Output current < I <sub>OL</sub>	Н	Н	L

Table 7. Electrical transient requirements on  $V_{CC}$  pin (part 1/3)

				··		
ISO T/R 7637/1 test pulse		Test levels				
	1	11	III	IV	Delays and impedance	
1	-25 V	-50 V	-75 V	-100 V	2 ms 10 Ω	
2	+25 V	+50 V	+75 V	+100 V	0.2 ms 10 Ω	
3a	-25 V	-50 V	-100 V	-150 V	0.1 μs 50 Ω	
3b	+25 V	+50 V	+75 V	+100 V	0.1 μs 50 Ω	
4	-4 V	-5 V	-6 V	-7 V	100 ms, 0.01 Ω	
5	+26.5 V	+46.5 V	+66.5 V	+86.5 V	400 ms, 2 Ω	

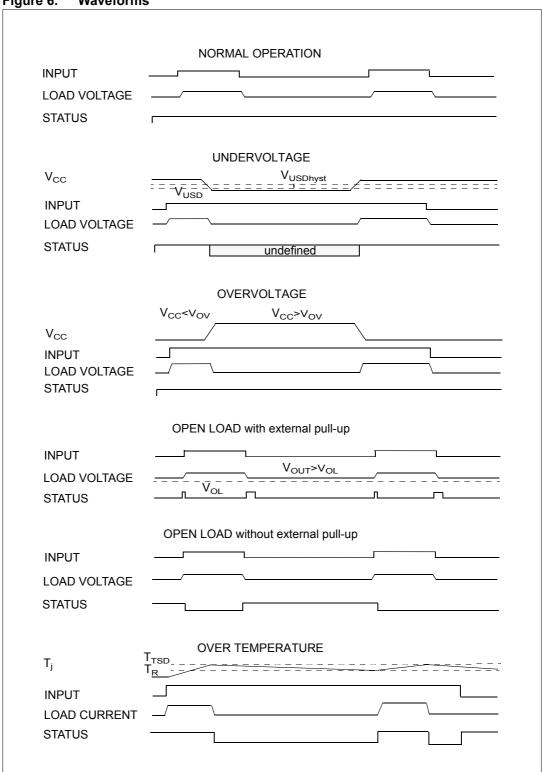
Table 8. Electrical transient requirements on V<sub>CC</sub> pin (part 2/3)

ISO T/R 7637/1 test pulse	Test levels results			
	I	II	III	IV
1	С	С	С	С
2	С	С	С	С
3a	С	С	С	С
3b	С	С	С	С
4	С	С	С	С
5	С	Е	Е	Е

Table 9. Electrical transient requirements on  $V_{CC}$  pin (part 3/3)

Class	Contents
С	All functions of the device are performed as designed after exposure to disturbance.
Е	One or more functions of the device is not performed as designed after exposure to disturbance and cannot be returned to proper operation without replacing the device.





#### 2.4 Electrical characteristics curves

Figure 7. Off-state output current

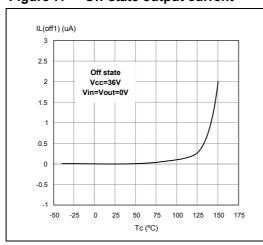


Figure 8. High level input current

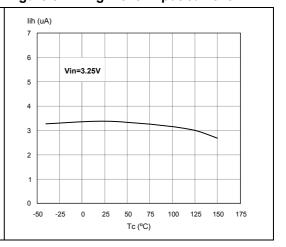


Figure 9. Input clamp voltage

Vicl (V)

8
7.8
7.6
7.4
7.2
7
6.8
6.6
6.4
6.2
6
-50 -25 0 25 50 75 100 125 150 175
Tc (°C)

Figure 10. Status leakage current

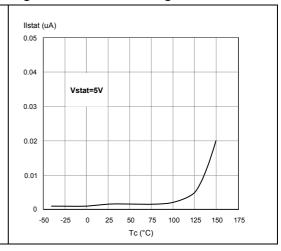


Figure 11. Status low output voltage

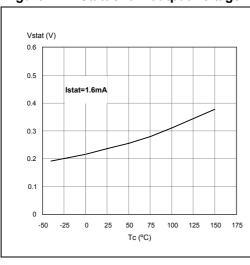
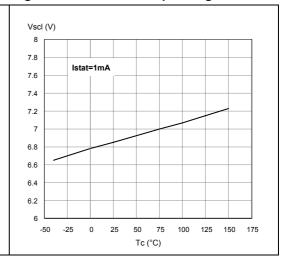


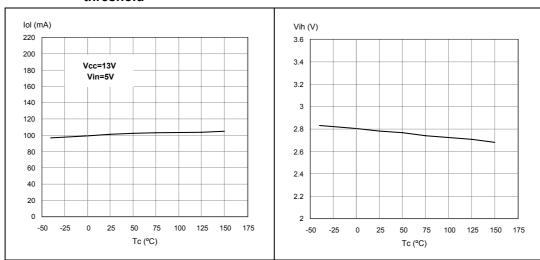
Figure 12. Status clamp voltage



Ron (mOhm) Ron (mOhm) 140 120 110 lout=2A lout=2A 100 Vcc=8V; 13V; 36V Tc= 150°C 100 90 80 80 Tc= 125°C 70 60 40 Tc= 25°C 40 20 Tc= - 40°C 30 40 Tc (°C) Vcc (V)

On-state resistance vs T<sub>case</sub> Figure 13. Figure 14. On-state resistance vs V<sub>CC</sub>

Open-load on-state detection Figure 16. Input high level Figure 15. threshold



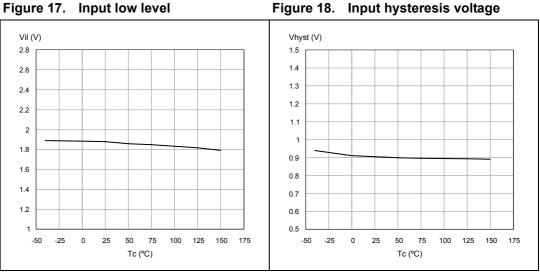
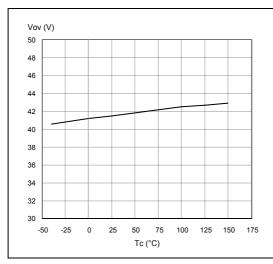


Figure 19. Overvoltage shutdown

Figure 20. Open-load off-state voltage detection threshold



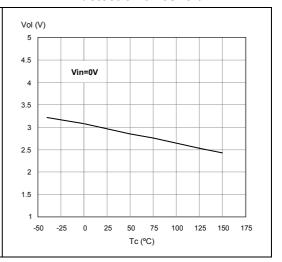
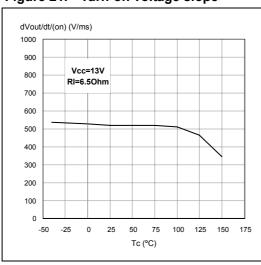


Figure 21. Turn-on voltage slope

Figure 22. Turn-off voltage slope



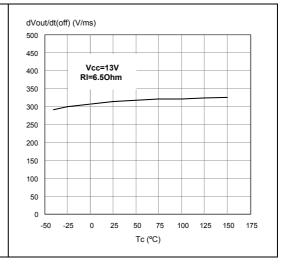
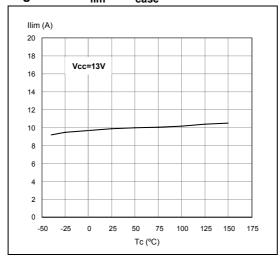


Figure 23. I<sub>lim</sub> vs T<sub>case</sub>



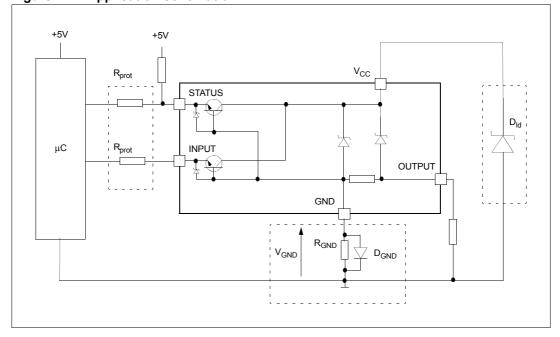


Figure 24. Application schematic

### 2.5 GND protection network against reverse battery

Solution 1: resistor in the ground line (R<sub>GND</sub> only). This can be used with any type of load.

The following is an indication on how to dimension the R<sub>GND</sub> resistor.

- 1.  $R_{GND} \le 600 \text{ mV} / (I_{S(on)max})$ .
- 2.  $R_{GND} \ge (-V_{CC}) / (-I_{GND})$

where -I<sub>GND</sub> is the DC reverse ground pin current and can be found in the absolute maximum rating section of the device datasheet.

Power dissipation in R<sub>GND</sub> (when V<sub>CC</sub> < 0: during reverse battery situations) is:

$$P_D = (-V_{CC})^2 / R_{GND}$$

This resistor can be shared amongst several different HSDs. Please note that the value of this resistor should be calculated with formula (1) where  $I_{S(on)max}$  becomes the sum of the maximum on-state currents of the different devices.

Please note that if the microprocessor ground is not shared by the device ground then the  $R_{GND}$  produces a shift ( $I_{S(on)max} * R_{GND}$ ) in the input thresholds and the status output values. This shift varies depending on how many devices are on in the case of several high side drivers sharing the same  $R_{GND}$ .

If the calculated power dissipation leads to a large resistor or several devices have to share the same resistor then ST suggests to utilize solution 2 (see below).

Solution 2: diode ( $D_{GND}$ ) in the ground line A resistor ( $R_{GND}$  =1  $k\Omega$ ) should be inserted in parallel to  $D_{GND}$  if the device drives an inductive load.

This small signal diode can be safely shared amongst several different HSDs. Also in this case, the presence of the ground network will produce a shift ( $\approx$ 600 mV) in the input threshold and in the status output values if the microprocessor ground is not common to the

device ground. This shift will not vary if more than one HSD shares the same diode/resistor network.

Series resistor in input and status lines are also required to prevent that, during battery voltage transient, the current exceeds the absolute maximum rating.

Safest configuration for unused input and status pin is to leave them unconnected.

### 2.6 Load dump protection

 $D_{ld}$  is necessary (voltage transient suppressor) if the load dump peak voltage exceeds the  $V_{CC}$  max DC rating. The same applies if the device is subject to transients on the  $V_{CC}$  line that are greater than the ones shown in the ISO 7637-2: 2004(E) table.

### 2.7 Microcontroller I/Os protection

If a ground protection network is used and negative transient are present on the  $V_{CC}$  line, the control pins will be pulled negative. ST suggests to insert a resistor ( $R_{prot}$ ) in line to prevent the microcontroller I/O pins to latch-up.

The value of these resistors is a compromise between the leakage current of microcontroller and the current required by the HSD I/Os (Input levels compatibility) with the latch-up limit of microcontroller I/Os.

 $-V_{CCpeak}/I_{latchup} \le R_{prot} \le (V_{OH\mu C}-V_{IH}-V_{GND}) / I_{IHmax}$ 

Calculation example:

For  $V_{CCpeak} = -100 \text{ V}$  and  $I_{latchup} \ge 20 \text{ mA}$ ;  $V_{OH\mu C} \ge 4.5 \text{ V}$ 

 $5 \text{ k}\Omega \leq R_{\text{prot}} \leq 65 \text{ k}\Omega.$ 

Recommended values:  $R_{prot} = 10 \text{ k}\Omega$ .

### 2.8 Open-load detection in off-state

Off-state open-load detection requires an external pull-up resistor ( $R_{PU}$ ) connected between output pin and a positive supply voltage ( $V_{PU}$ ) like the +5V line used to supply the microprocessor.

The external resistor has to be selected according to the following requirements:

- 1. no false open-load indication when load is connected: in this case we have to avoid  $V_{OUT}$  to be higher than  $V_{Olmin}$ ; this results in the following condition  $V_{OUT} = (V_{PU} / (R_L + R_{PU}))R_L < V_{Olmin}$ .
- 2. no misdetection when load is disconnected: in this case the  $V_{OUT}$  has to be higher than  $V_{OLmax}$ ; this results in the following condition  $R_{PU} < (V_{PU} V_{OLmax}) / I_{L(off2)}$ .

Because  $I_{s(OFF)}$  may significantly increase if  $V_{out}$  is pulled high (up to several mA), the pull-up resistor  $R_{PU}$  should be connected to a supply that is switched off when the module is in standby.

The values of  $V_{OLmin}$ ,  $V_{OLmax}$  and  $I_{L(off2)}$  are available in the electrical characteristics section.

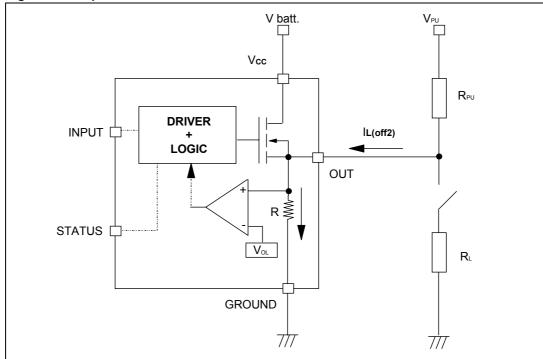
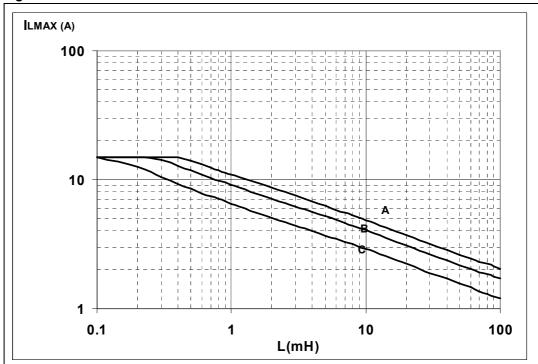


Figure 25. Open-load detection in off-state

#### SO-8 maximum demagnetization energy ( $V_{CC} = 13.5 \text{ V}$ ) 2.9

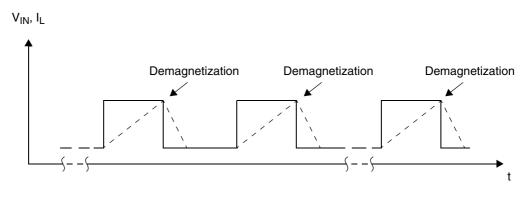
Figure 26. SO-8 maximum turn-off current versus inductance



A: T<sub>istart</sub> = 150 °C single pulse

B: T<sub>jstart</sub> = 100 °C repetitive pulse

C: T<sub>istart</sub> = 125 °C repetitive pulse



Note: Values are generated with  $R_L$  =0  $\Omega$ In case of repetitive pulses,  $T_{jstart}$  (at beginning of each demagnetization) of every pulse must not exceed the temperature specified above for curves A and B.

## 3 Package and PCB thermal data

#### 3.1 SO-8 thermal data

Figure 27. PC board

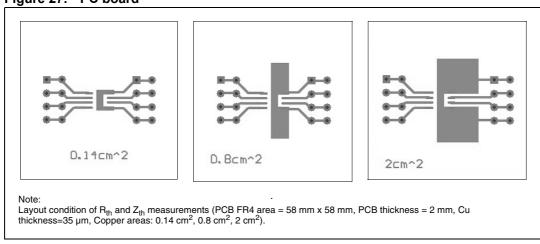
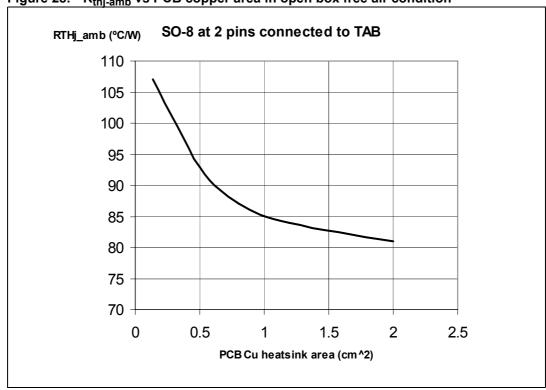


Figure 28. R<sub>thi-amb</sub> vs PCB copper area in open box free air condition



20/27 Doc ID 16782 Rev 2

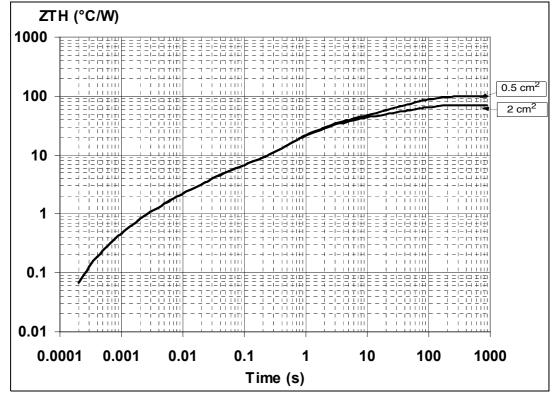


Figure 29. SO-8 thermal impedance junction ambient single pulse

#### **Equation 1: pulse calculation formula**

$$\begin{split} Z_{TH\delta} &= R_{TH} \cdot \delta + Z_{THtp} (1 - \delta) \\ \text{where } \delta &= t_P / T \end{split}$$

Figure 30. Thermal fitting model of a single channel

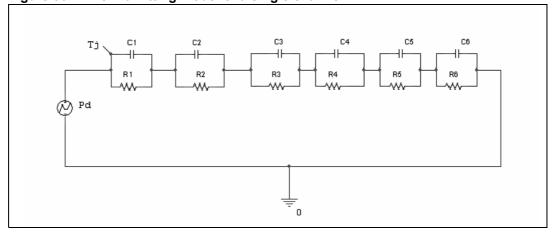


Table 10. Thermal parameter

Area/island (cm <sup>2</sup> )	0.5	2
R1 (°C/W)	0.05	
R2 (°C/W)	0.8	
R3 (°C/W)	3.5	
R4 (°C/W)	21	
R5 (°C/W)	16	
R6 (°C/W)	58	28
C1 (W·s/°C)	0.006	
C2 (W·s/°C)	0.0026	
C3 (W·s/°C)	0.0075	
C4 (W·s/°C)	0.045	
C5 (W·s/°C)	0.35	
C6 (W·s/°C)	1.05	2

## 4 Package and packing information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: <a href="https://www.st.com">www.st.com</a>.

ECOPACK® is an ST trademark.

### 4.1 SO-8 package information

Figure 31. SO-8 package dimensions

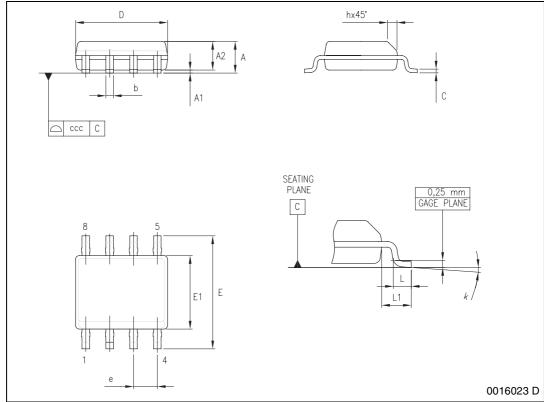


Table 11. SO-8 mechanical data

Dim.	mm			
	Min.	Тур.	Max.	
A			1.75	
A1	0.10		0.25	
A2	1.25			
b	0.28		0.48	
С	0.17		0.23	
D <sup>(1)</sup>	4.80	4.90	5.00	
E	5.80	6.00	6.20	
E1 <sup>(2)</sup>	3.80	3.90	4.00	
е		1.27		
h	0.25		0.50	
L	0.40		1.27	
L1		1.04		
k	0°		8°	
ccc			0.10	

Dimension "D" does not include mold flash, protrusions or gate burrs. Mold flash, protrusions or gate burrs shall not exceed 0.15 mm in total (both side).

<sup>2.</sup> Dimension "E1" does not include interlead flash or protrusions. Interlead flash or protrusions shall not exceed 0.25 mm per side.

### 4.2 SO-8 packing information

The devices can be packed in tube or tape and reel shipments (see the *Device summary on page 1*).

Figure 32. SO-8 tube shipment (no suffix)

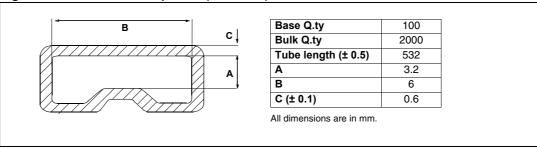
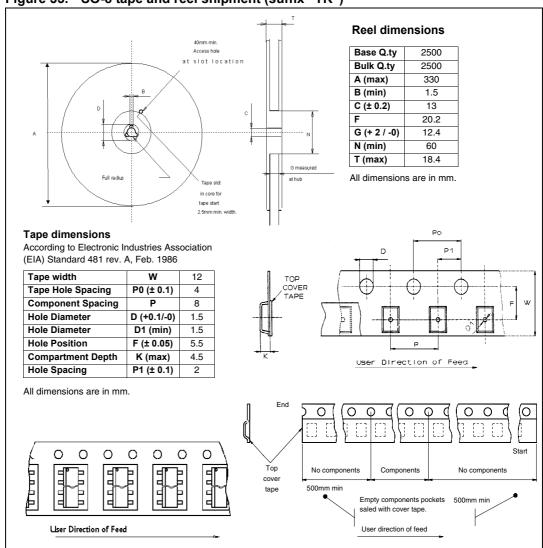


Figure 33. SO-8 tape and reel shipment (suffix "TR")



Revision history VN750PS-E

# 5 Revision history

Table 12. Document revision history

Date	Revision	Changes	
23-Nov-2009	1	Initial release.	
15-Oct-2010	2	Updated Table 4: Thermal data Updated following figure titles:  - Figure 21: Turn-on voltage slope  - Figure 22: Turn-off voltage slope	

#### Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY AN AUTHORIZED ST REPRESENTATIVE, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2010 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Philippines - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com



Doc ID 16782 Rev 2